



## SILICON N-CHANNEL JUNCTION-TYPE FIELD EFFECT TRANSISTOR FOR CONDENSER MICROPHONE IMPEDANCE CONVERSION

### ABSOLUTE MAXIMUM RATINGS/T<sub>a</sub> = 25°C

			unit
Drain-gate voltage	V <sub>DGO</sub>	20	V
Gate current	I <sub>G</sub>	10	mA
Allowable power dissipation	P <sub>D</sub>	100	mW
Junction temperature	T <sub>j</sub>	125	°C
Storage ambient temperature	T <sub>stg</sub>	-40 ~ +125	°C

### ELECTRICAL CHARACTERISTICS/T<sub>a</sub> = 25°C

			min	typ	max	unit
Drain current	I <sub>DSS*</sub>	V <sub>DS</sub> = 10 V	0.06*		1.5*	mA

[T<sub>a</sub> = 25°C, V<sub>CC</sub> = 4.5 V, R<sub>D</sub> = 680 Ω, C<sub>in</sub> = 15 pF, in specified test circuit (conforming with application circuit)]

			min	typ	max	unit
Transmission loss voltage-drop characteristics	△G <sub>VV</sub>	V <sub>cc</sub> = 4.5 ~ 1.5 V, f = 1 kHz			-3	dB
Transmission loss frequency characteristics	△G <sub>Vf</sub>	f = 1 k ~ 110 Hz, V <sub>in</sub> = 10 mV			-1	dB
Input impedance	z <sub>in</sub>	f = 1 kHz	20 M			Ω
Output noise voltage	V <sub>NO</sub>	V <sub>in</sub> = 0, A-curve			-110	dB

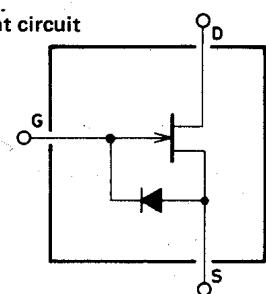
\* 2SK156 is graded as follows by drain current I<sub>DSS</sub>:

0.06	A	0.3	0.25	B	0.8	0.6	C	1.5
------	---	-----	------	---	-----	-----	---	-----

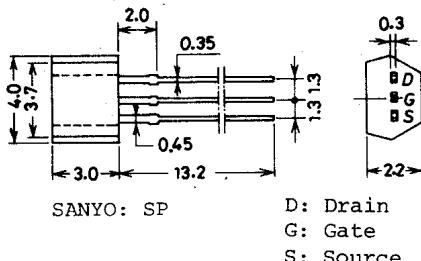
J	K	L	M
60 - 180	150 - 300	250 - 450	400 - 800

(μA)

Equivalent circuit



Case Outline 2001  
(unit: mm)



These specifications are subject to change without notice.